

# 2SK2047

## Silicon N-Channel Power F-MOS

### ■ Features

- Avalanche energy capability guaranteed : EAS > 3.6mJ
- $V_{GSS} = \pm 30V$  guaranteed
- High-speed switching :  $t_f = 30ns$
- No secondary breakdown

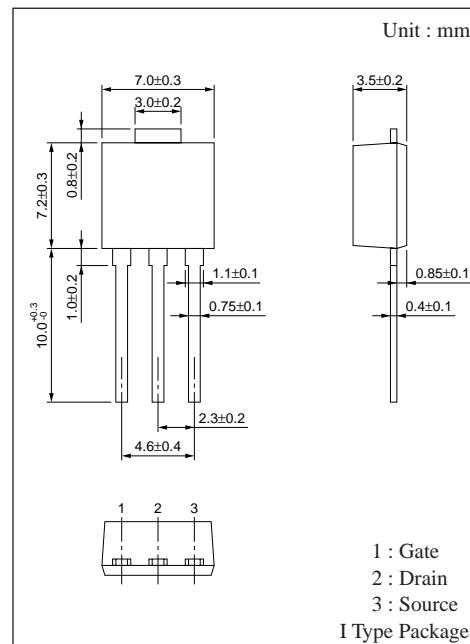
### ■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

### ■ Absolute Maximum Ratings ( $T_c = 25^\circ C$ )

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	$V_{DSS}$	550	V
Gate-Source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	DC $I_D$	$\pm 1.2$	A
	Pulse $I_{DP}$	$\pm 3.6$	A
Avalanche energy capability	EAS *	3.6	mJ
Allowable power dissipation	$T_c = 25^\circ C$ $P_D$	15	W
	$T_a = 25^\circ C$	1.3	
Channel temperature	$T_{ch}$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\*  $L = 5mH$ ,  $I_L = 1.2A$ ,  $V_{DD} = 50V$ , 1 pulse

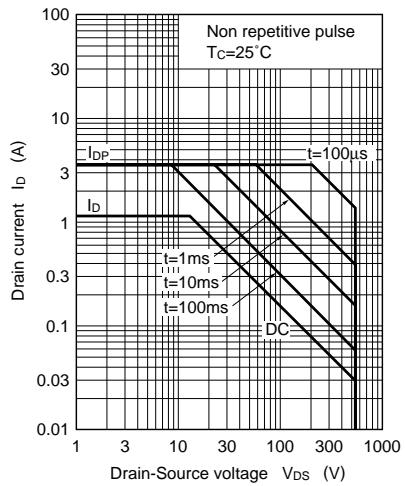
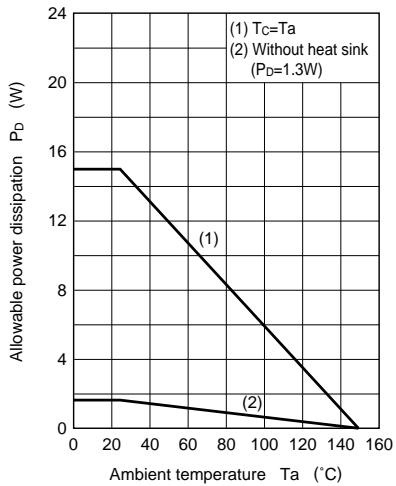
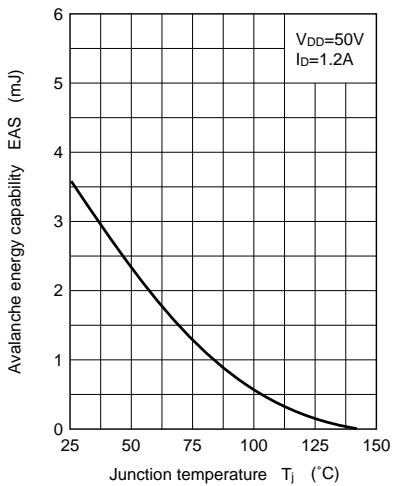
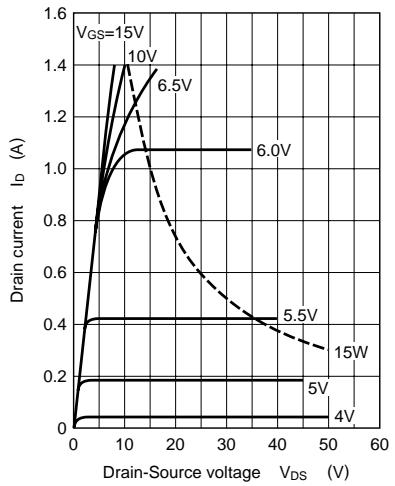
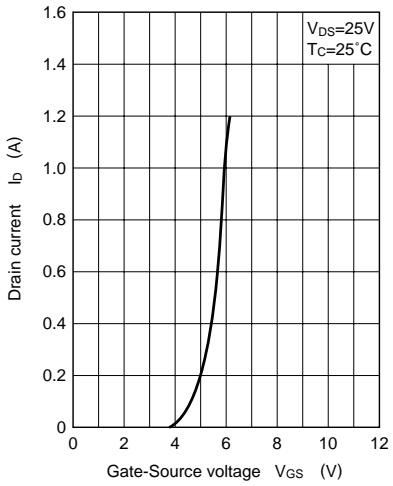
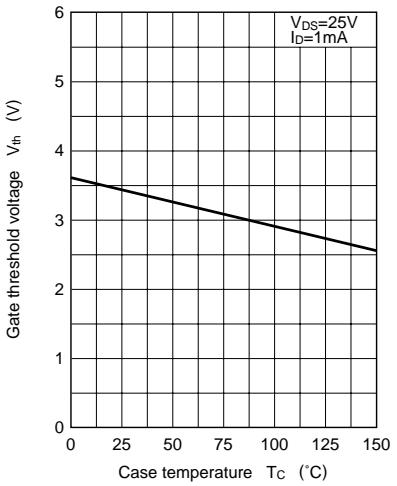
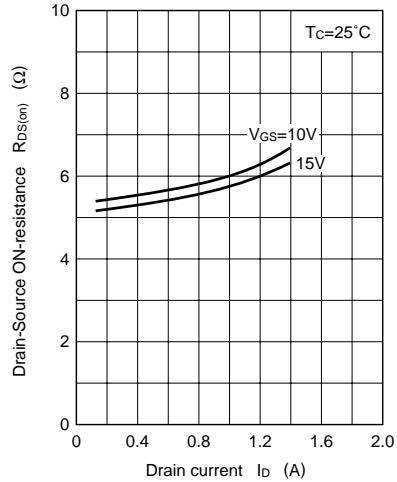
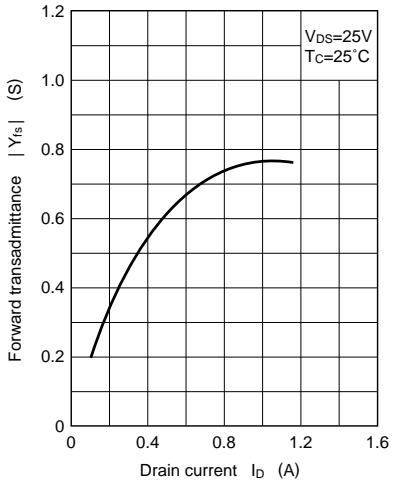
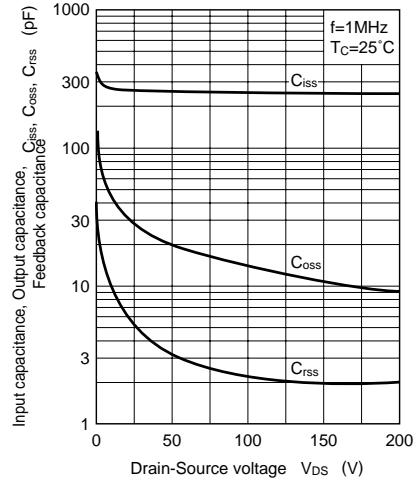


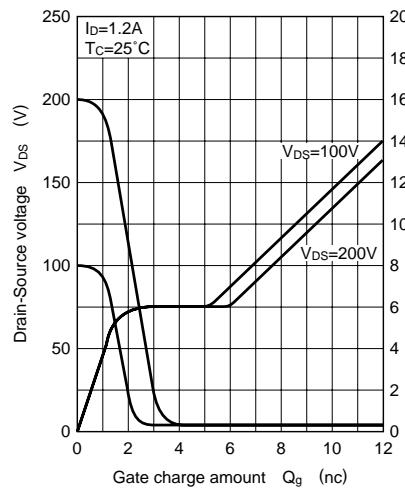
1 : Gate  
2 : Drain  
3 : Source  
I Type Package

### ■ Electrical Characteristics ( $T_c = 25^\circ C$ )

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	$I_{DSS}$	$V_{DS} = 440V$ , $V_{GS} = 0$			0.1	mA
Gate-Source leakage current	$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0$			$\pm 1$	$\mu A$
Drain-Source breakdown voltage	$V_{DSS}$	$I_D = 1mA$ , $V_{GS} = 0$	550			V
Gate threshold voltage	$V_{th}$	$V_{DS} = 25V$ , $I_D = 1mA$	2		5	V
Drain-Source ON-resistance	$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.6A$		5.3	8	$\Omega$
Forward transadmittance	$ Y_{fs} $	$V_{DS} = 25V$ , $I_D = 0.6A$	0.4	0.65		S
Diode forward voltage	$V_{DSF}$	$I_{DR} = 1.2A$ , $V_{GS} = 0$			-1.5	V
Input capacitance	$C_{iss}$	$V_{DS} = 20V$ , $V_{GS} = 0$ , $f = 1MHz$		290		pF
Output capacitance	$C_{oss}$			40		pF
Feedback capacitance	$C_{rss}$			10		pF
Turn-on time (delay time)	$t_{d(on)}$	$V_{GS} = 10V$ , $I_D = 0.6A$ $V_{DD} = 150V$ , $R_L = 250\Omega$		15		ns
Rise time	$t_r$			20		ns
Fall time	$t_f$			30		ns
Turn-off time (delay time)	$t_{d(off)}$			70		ns
Channel-Case heat resistance	$R_{th(ch-c)}$				8.33	$^\circ C/W$

Area of safe operation (ASO)

P<sub>D</sub> – TaEAS – T<sub>j</sub>I<sub>D</sub> – V<sub>DS</sub>I<sub>D</sub> – V<sub>GS</sub>V<sub>th</sub> – T<sub>C</sub>R<sub>DS(on)</sub> – I<sub>D</sub>|Y<sub>fs</sub>| – I<sub>D</sub>C<sub>iss</sub>, C<sub>oss</sub>, C<sub>rss</sub> – V<sub>DS</sub>

$V_{DS}, V_{GS} - Q_g$  $t_{d(on)}, t_r, t_f, t_{d(off)} - I_D$ 